**Product data sheet** 

## 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

## 2. Features and benefits

- · Fast switching
- Low thermal resistance
- High thermal cycling performance
- Low forward voltage drop
- Reverse surge capability
- · Soft recovery characteristic

## 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		200				V
I <sub>O(AV)</sub>	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 104$ °C; both diodes conducting; Fig. 1; Fig. 2	16			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 104 °C; square-wave pulse; per diode	16			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; per diode $T_{j(init)}$ = 25 °C				А	
		$t_p$ = 8.3 ms; sine-wave pulse; per diode $T_{j(init)}$ = 25 °C			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	0.84	0.95	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	ne $I_R = 1 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; \frac{\text{Fig. 6}}{\text{C}}$		-	12	22	ns

**Dual ultrafast power diode** 

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	7 7	4
3	A2	anode 2		A1 A2
mb	K	mounting base; cathode		K sym125

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	Package						
	Name	Description	Version					
BYQ30E-200	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78					

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BYQ30E-200	BYQ30E-200

**Dual ultrafast power diode** 

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		200	V
$V_{RWM}$	crest working reverse voltage		200	V
$V_R$	reverse voltage	DC	200	V
$I_{O(AV)}$	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 104 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u>	16	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 104 °C$ ; square-wave pulse; per diode	16	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; sine-wave pulse; per diode $T_{j(init)}$ = 25 °C	80	А
		$t_p$ = 8.3 ms; sine-wave pulse; per diode $T_{j(init)}$ = 25 °C	88	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; $t_p$ = 2 $\mu$ s	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	$t_p = 100 \ \mu s$	0.2	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C
Electrosta	tic discharge			
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 kΩ	8	kV

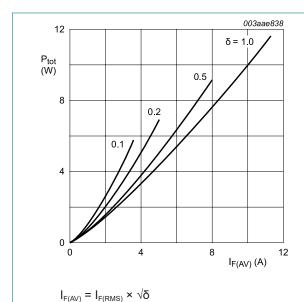
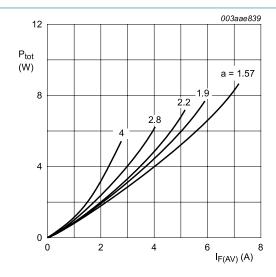


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$ 

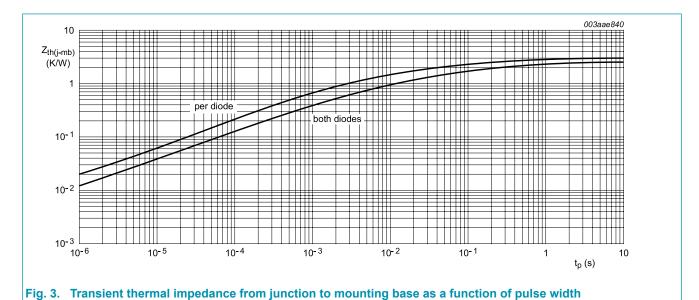
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

**Dual ultrafast power diode** 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; both diodes conducting; <u>Fig. 3</u>	-	-	2.5	K/W
	mounting base	with heatsink compound; per diode; <u>Fig. 3</u>	-	-	3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	60	-	K/W

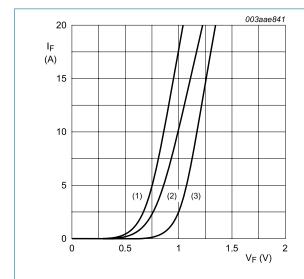


**Dual ultrafast power diode** 

## 10. Characteristics

### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub> forv	forward voltage	I <sub>F</sub> = 16 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	1	1.15	V
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.12	1.25	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.84	0.95	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	4	30	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.3	0.6	mA
Dynamic	characteristics			'		
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/µs};$ $T_j = 25 \text{ °C}; Fig. 5$	-	4	11	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/µs}$ ; ramp recovery; $T_j = 25 \text{ °C}$ ; Fig. 5	-	20	25	ns
		$I_F = 0.5 \text{ A}$ ; $I_R = 1 \text{ A}$ ; step recovery; $I_{R(meas)} = 0.25 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; Fig. 6	-	12	22	ns
$V_{FR}$	forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}I_F/\text{d}t = 10 \text{ A}/\mu\text{s}; T_j = 25 °C;$ Fig. 7	-	1	-	V



(1) T<sub>j</sub> = 150 °C; typical values (2) T<sub>j</sub> = 150 °C; maximum values

(3)  $T_i = 25$  °C; maximum values



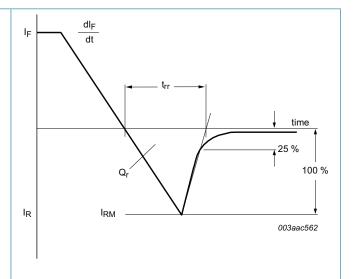
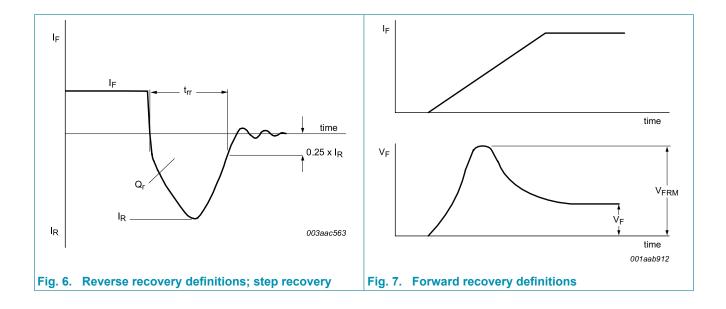


Fig. 5. Forward recovery definitions; ramp recovery

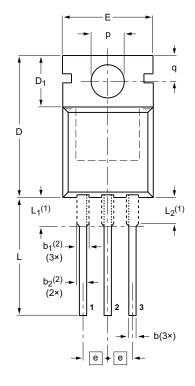
**Dual ultrafast power diode** 

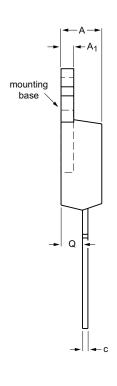


# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 







### **DIMENSIONS** (mm are the original dimensions)

UNIT	А	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

### Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

WeEn Semiconductors BYQ30E-200

**Dual ultrafast power diode** 

# 12. Revision history

### **Table 8. Revision history**

	•								
Document ID	Release date	Data sheet status	Change notice	Supersedes					
BYQ30E-200 v.5	20180605	Product data sheet	-	BYQ30E-200 v.4					
Modifications:	Modifications: Change from NXP version to WeEn version								
BYQ30E-200 v.4	20100901	Product data sheet	-	BYQ30E_SERIES_3					
Modifications:  • The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.  • Legal texts have been adapted to the new company name where appropriate.  • Type number BYQ30E-200 separated from datasheet BYQ30E SERIES.									
BYQ30E_SERIES_3	19981001	Product specification	-	BYQ30E_SERIES_2					

### **Dual ultrafast power diode**

## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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5 June 2018

WeEn Semiconductors BYQ30E-200

**Dual ultrafast power diode** 

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## **Dual ultrafast power diode**

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